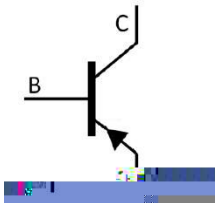


VRW0; < ММ Ё SQS æ М ы s ll 1 Silicon PNP transistor in a SOT-89 Plastic Package.

η 3 М Ё /ъ NWF76:9 Ы ´
 Small flat package, complementary to KTC4376.

℥ˆˆ z ɔ ll ˆ ˆ z
 High current application.



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

h_{FE} Classifications Symbol	O	Y
h_{FE} Range	100 200	160 320
Marking	HRO*	HR Y*

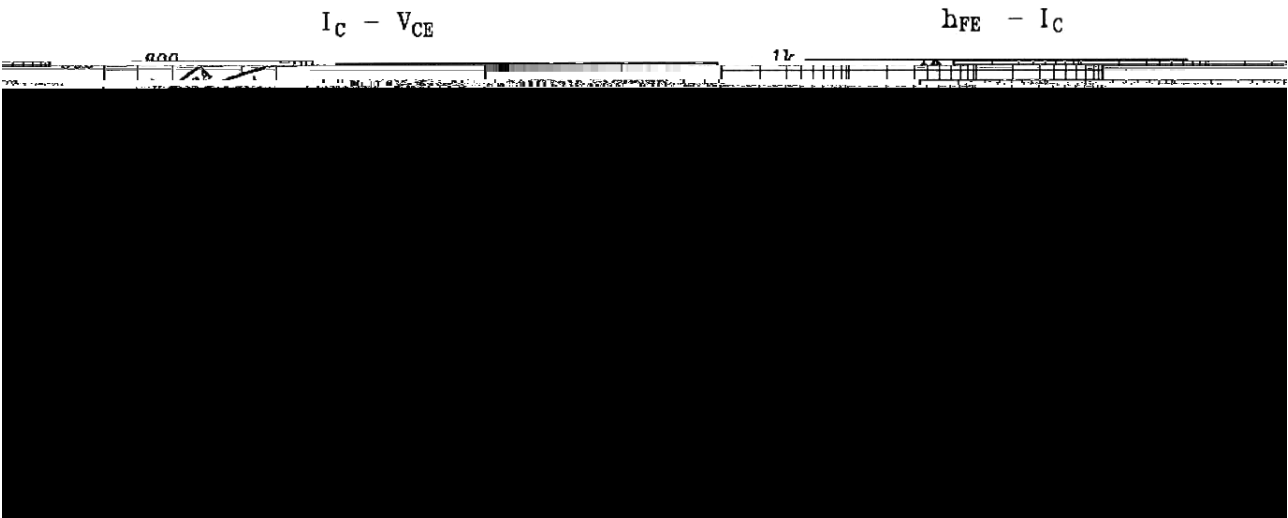
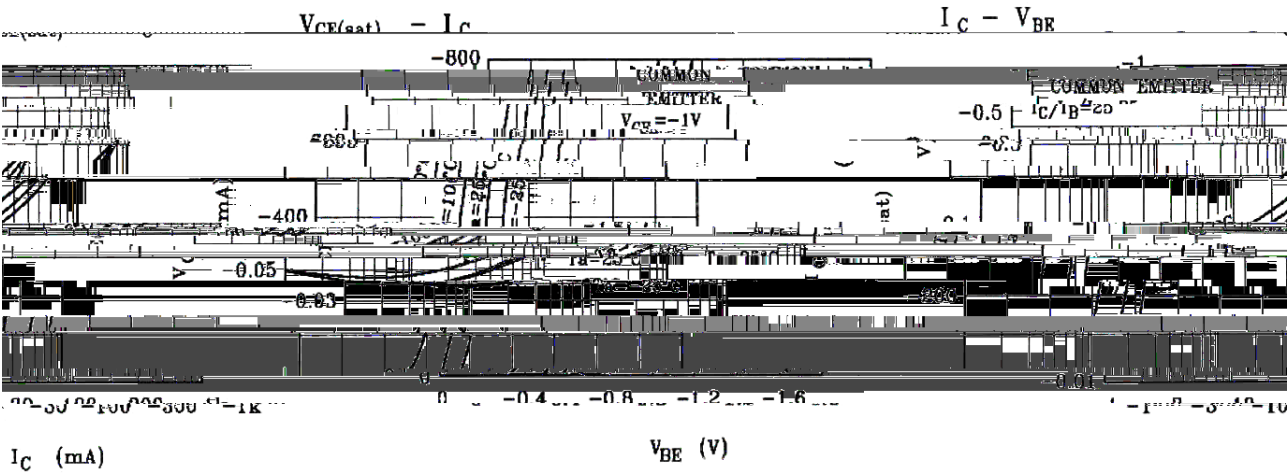
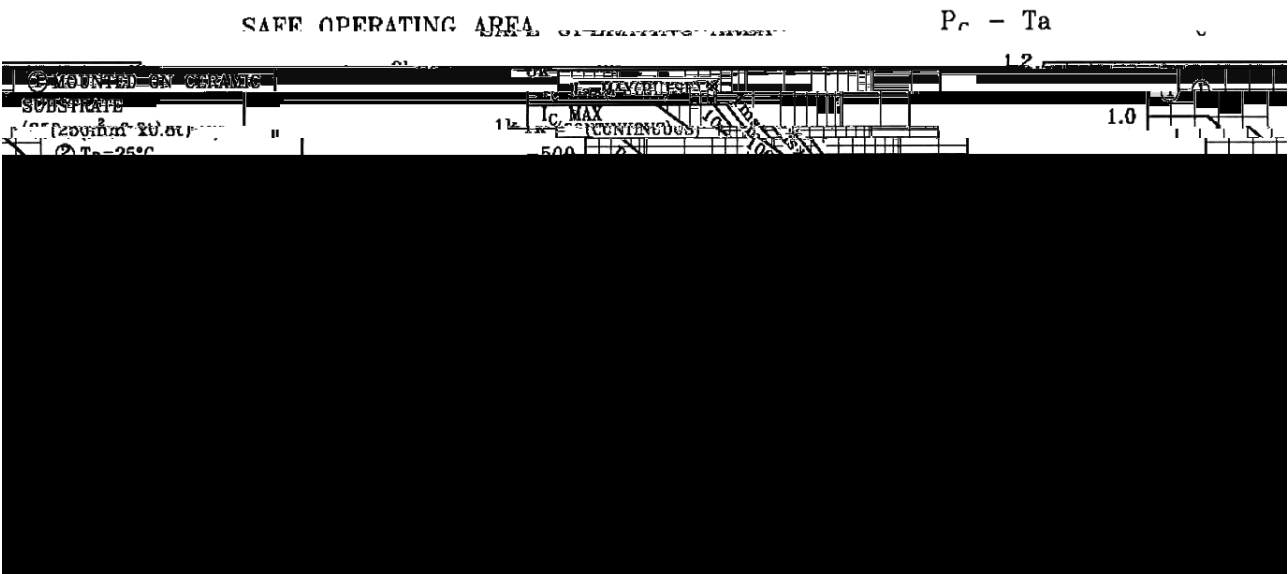
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-35	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-800	mA
Collector Base – Continuous	I_B	-160	mA
Collector Power Dissipation	P_C	500	mW
Collector Power Dissipation*	$*P_C$	1.0	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

*:mounted on ceramic substrate(250mm²×0.8t)

- 583 p p 5031; W 0031 i

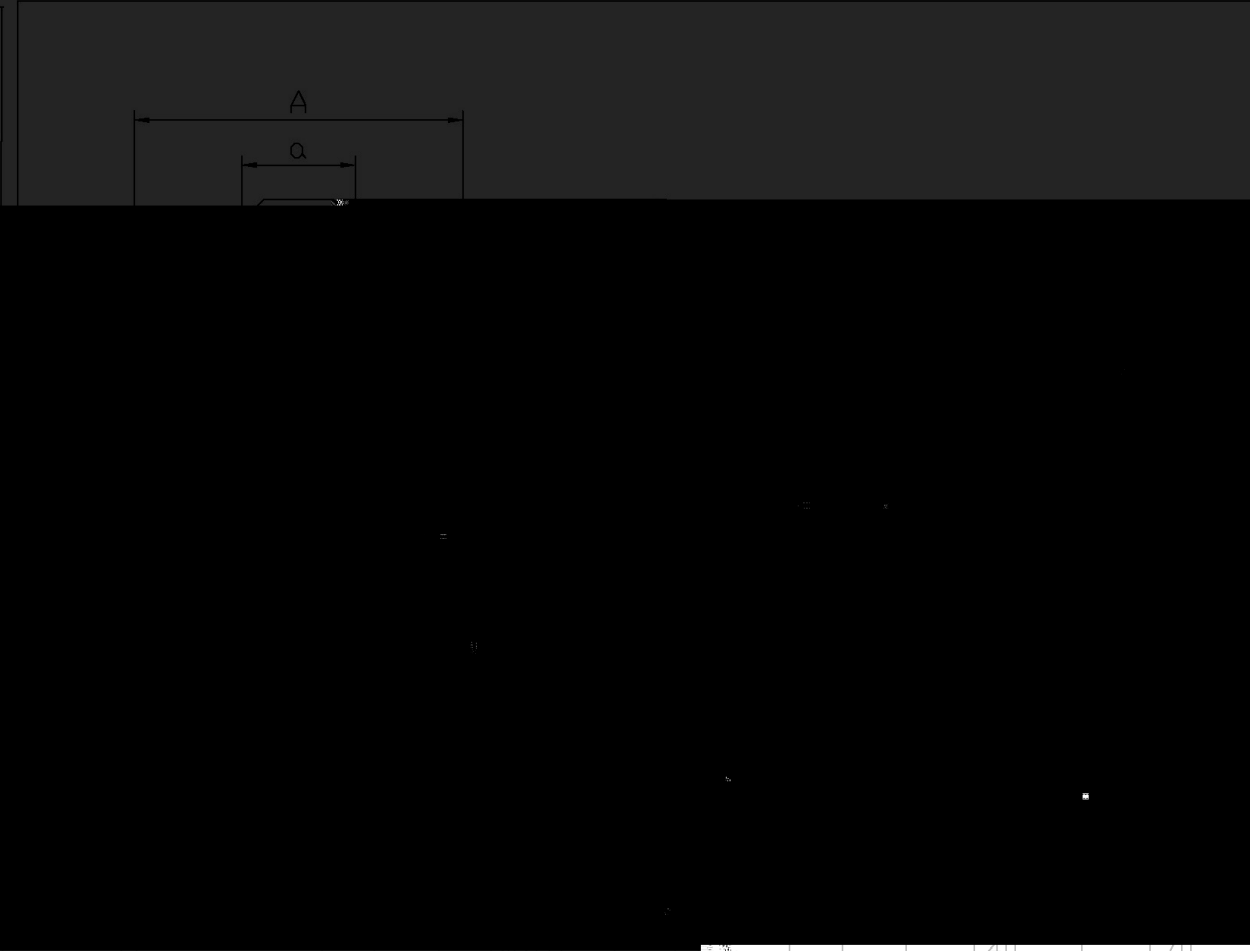
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-10mA$ $I_B=0$	-30			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-35V$ $I_E=0$			-0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=-5.0V$ $I_C=0$			-0.1	μA

DC Current Gain $h_{FE(1)}$ V_{CE}



STT-89

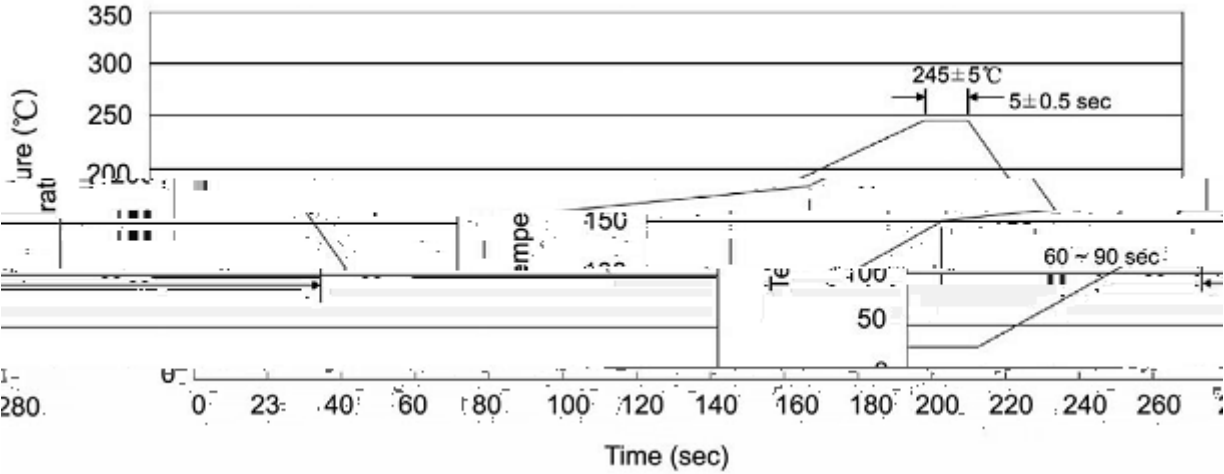
单位: mm



E	1.40	1.70	C	1.40	1.70
a	1.45	1.65	c1	0.35	0.50
E	1.40	1.60	P	6°	
F1	2.50	3.20			
b	0.80	1.20			



Lot No. Code, code change with Lot No.



1. 预加热: 25~150 °C, Time: 60~90sec;

2. 峰值温度: 245±5 °C, 持续时间: 5±0.5sec;

3. 冷却速度: 2~10 °C/sec.
- Note:

1.Preheating:25~150 °C , Time:60~90sec.

2.Peak Temp.:245 °C , Duration:5 ± 0.5sec.

3. Cooling Speed: 2~10 °C /sec.

锡焊: 260±5 °C, Time: 10±1 sec. Temp.:260±5 Time:10±1 sec

包装形式 / REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel	Reels/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Reel	Inner Box	Outer Box
SOT-89	1,000	7	7,000	8	56,000	7 ×12	180×120×180	385×257×392